

2SA1698

Silicon PNP Epitaxial Planar Type

General Amplifier
Complementary Pair with 2SC2258

■ Feature

- High collector-emitter voltage (V_{CE0})

■ Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-300	V
Collector-emitter voltage	V_{CEO}	-300	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-100	mA
Collector current	I_C	-70	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

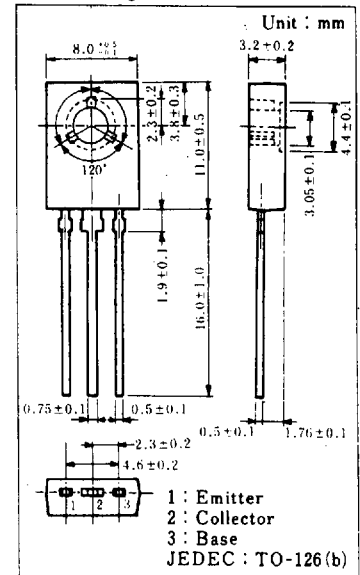
■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

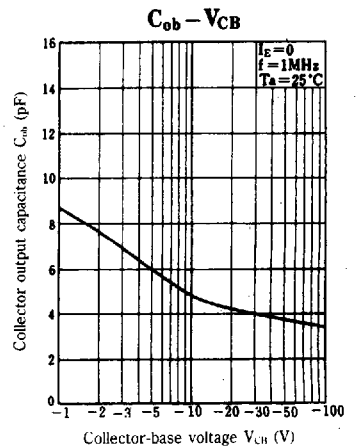
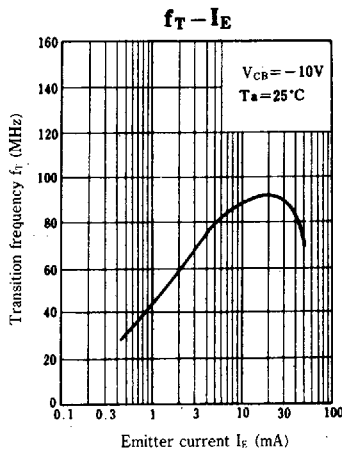
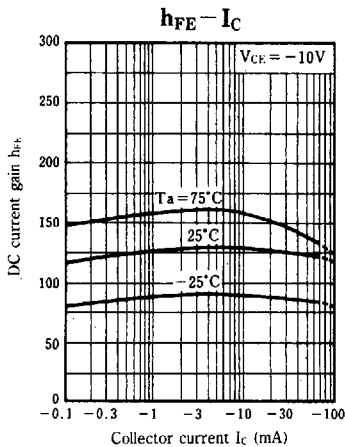
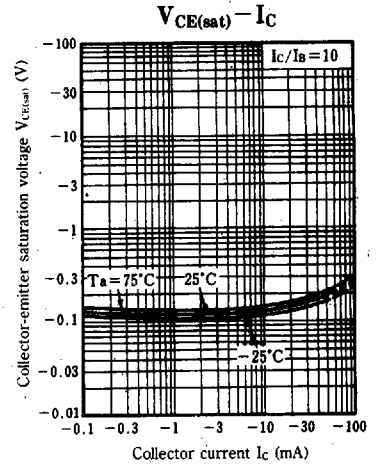
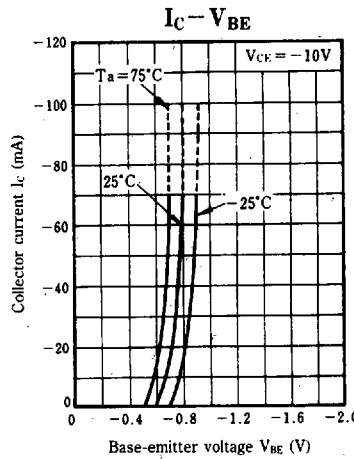
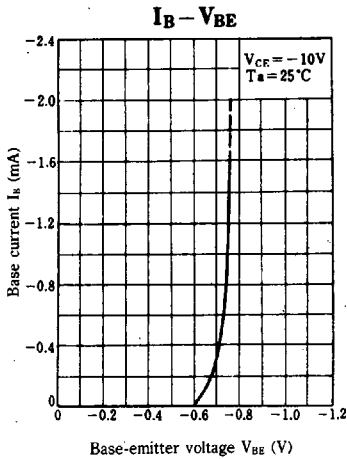
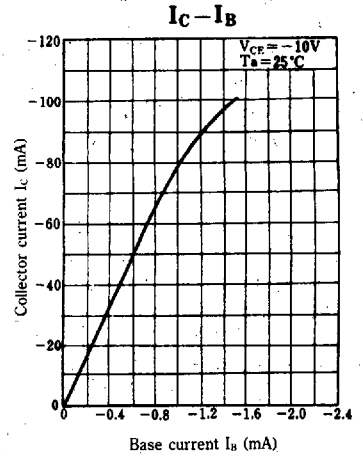
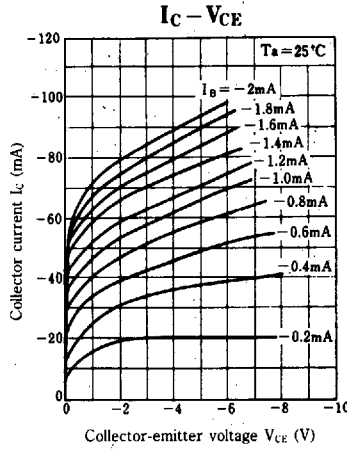
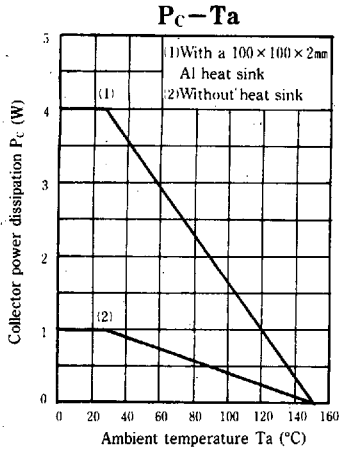
Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = -120\text{V}, I_B = 0$			-1	μA
Collector-emitter voltage	V_{CEO}	$I_C = -100\mu\text{A}, I_B = 0$	-300			V
Emitter-base voltage	V_{EBO}	$I_E = -1\mu\text{A}, I_C = 0$	-5			V
DC current gain	h_{FE}^*	$V_{CE} = -10\text{V}, I_C = -5\text{mA}$	30		220	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-1.5	V
Transition frequency	f_T	$V_{CB} = -10\text{V}, I_E = 10\text{mA}, f = 200\text{MHz}$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			10	pF

* h_{FE} Classifications

Class	P	Q	R
h_{FE}	30~100	60~150	100~220

■ Package Dimensions





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